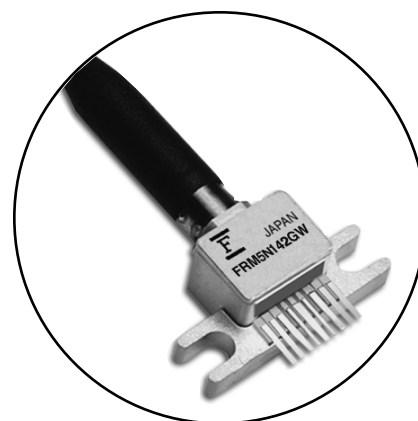


FEATURES

- Small Form Factor Package(GW): 9 pins coplanar
- Integrated Design Optimizes Performance at Bit Rates up to 10.7Gb/s
- High Gain: 4k Ω (Single-ended), 8k Ω (Differential)
- High Sensitivity: -27dBm (typ.)
- Electrical Differential Output
- Wide Bandwidth: 8.5GHz (typ.)
- Operates in both C and L wavelength bands
- Wide Operating Temperature Range: -5°C to +75°C



APPLICATIONS

This APD with HBT preamplifier is intended to function as an optical receiver at 1,310nm or 1,530-1,610nm in SONET, SDH, DWDM or other optical fiber systems operating up to 10.7Gb/s. The typical transimpedance (Z_t) value of 4,000 Ω optimizes the total bandwidth for 10Gb/s application. The detector preamplifier is DC coupled and has an electrical differential output.

DESCRIPTION

The FRM5N142GW incorporates a high bandwidth InGaAs APD photo diode, a GaAs HBT IC amplifier in a hermetically sealed Small Form Factor package (SFF). The APD is processed with modern MOVPE techniques resulting in a reliable performance over a wide range of operating conditions. The lens coupling system and the single mode fiber are assembled using Nd YAG welding.

ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Storage Temperature	T_{stg}	-40 to +85	$^\circ\text{C}$
Operating Temperature	T_{op}	-5 to +75	$^\circ\text{C}$
Supply Voltage	V_{ss}	-6 to 0	V
PIN Reverse Voltage	V_R	0 to V_B (Note)	V
PIN Reverse Current	$I_{R(peak)}$	5	mA

Note: Since V_B may vary from device-to-device, V_B data is attached to each device for reference.

OPTICAL & ELECTRICAL CHARACTERISTICS

(T_C=25°C, λ=1,550nm, V_{SS}=-5.2V, unless otherwise specified)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
APD Responsivity	R13	λ = 1,310nm, M=1	0.70	0.85	-	A/W
	R15	λ = 1,550nm, M=1	0.70	0.90	-	
	R16	λ = 1,610nm, M=1	-	0.80	-	
APD Breakdown Voltage	VB	ID = 10μA	20.0	25.0	30.0	V
Temperature Coefficient of VB	γ	Note (1)	0.03	0.05	0.07	V/°C
AC Transimpedance	Z _t	f = 750MHz, Single-end	3500	4000	-	Ω
Maximum Output Voltage Swing	V _{clip}	Saturated Output Voltage, Single-ended	250	350	450	mV
Bandwidth	BW	-3dB from 750MHz, Pin=-24dBm, M=9	7.5	8.5	-	GHz
		M=3	7.5	8.5	-	
Lower Cut-off Frequency	f _{cl}	-3dB from 750MHz, Pin=-24dBm	-	40	100	kHz
Peaking	d _{pk}	130MHz to BW, Pin=-24dBm, M=9	-	1.5	2.0	dB
Group Delay Deviation	GD	1GHz to 6GHz, Pin=-24dBm, M=9	-	30	-	ps _{p-p}
		1GHz to 8GHz, Pin=-24dBm, M=9	-	60	-	
Output Return Loss	S ₂₂	130MHz to 6GHz	-	10	-	dB
		130MHz to 8GHz	-	7	-	
Minimum Sensitivity	P _r	10Gb/s, NRZ, 25°C, R _{ext} =13dB	-	-27.0	-25.0	dBm
		PRBS=2 ³¹ -1, 25°C, R _{ext} =10dB	-	-26.0	-	
		B.E.R.=10 ⁻¹² , 25°C, R _{ext} =8.2dB	-	-25.0	-	
		VR=Optimum, 75°C, R _{ext} =13dB	-	-26.0	-24.0	
Maximum Overload	P _o	10Gb/s, NRZ, PRBS=2 ³¹ -1, B.E.R.=10 ⁻¹² , R _{ext} =13dB, M=3	-4	-2	-	dBm
Optical Return Loss	ORL	λ = 1,550nm	27	-	-	dB
		λ = 1,310nm	27	-	-	
Power Supply Current	I _{ss}	-	-	80	130	mA
Power Supply Voltage	V _{ss}	-	-5.46	-5.20	-4.94	V
Thermistor Resistance	R _{th}	-	9.5	10.0	10.5	kΩ
Thermistor B Constant	B	-	3800	3900	4000	K

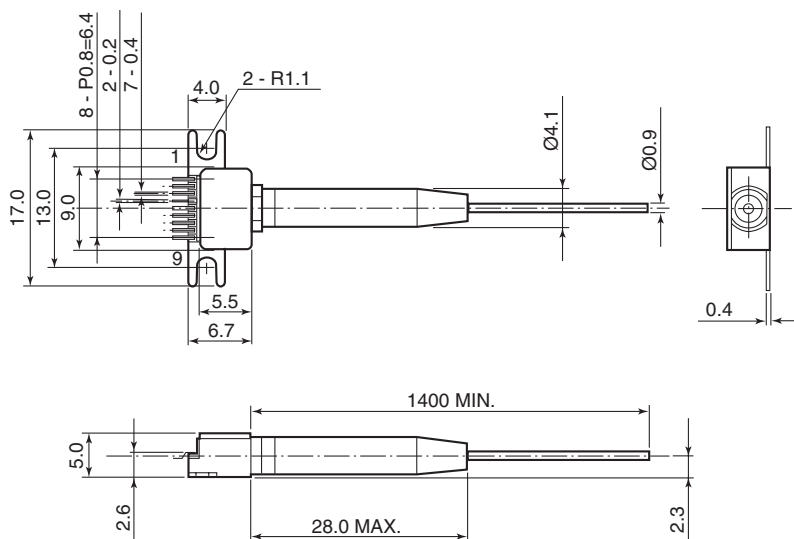
Note 1: γ=ΔVB/ΔT_C

Note: All the parameters are measured with 50Ω, AC-coupled.

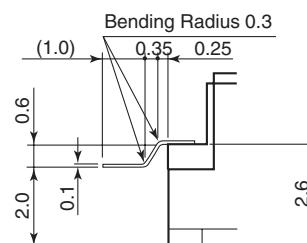
Notes

"GW" PACKAGE

UNIT: mm



Lead Detail (x10)



PIN #	Symbol	Function
1	VPD	PD BIAS (+)
2	Vpreamp	Preamp BIAS
3	GND	CASE GROUND
4	OUT	OUTPUT (-)
5	GND	CASE GROUND
6	OUT	OUTPUT (+)
7	GND	CASE GROUND
8	-	NC
9	Rth	THERMISTOR

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- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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